捷多邦,专业PCB打样SN54AH@TOO世SN74AHCT00 QUADRUPLE 2-INPUT POSITIVE-NAND GATES

SCLS229H - OCTOBER 1995 - REVISED JANUARY 2000

- EPIC™ (Enhanced-Performance Implanted CMOS) Process
- Inputs Are TTL-Voltage Compatible
- Latch-Up Performance Exceeds 250 mA Per JESD 17
- ESD Protection Exceeds 2000 V Per MIL-STD-883, Method 3015; Exceeds 200 V Using Machine Model (C = 200 pF, R = 0)
- Package Options Include Plastic Small-Outline (D), Shrink Small-Outline (DB), Thin Very Small-Outline (DGV), Thin Shrink Small-Outline (PW), and Ceramic Flat (W) Packages, Ceramic Chip Carriers (FK), and Standard Plastic (N) and Ceramic (J) DIPs

description

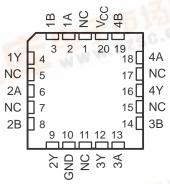
The 'AHCT00 devices perform the Boolean function $Y = \overline{A} \bullet \overline{B}$ or $Y = \overline{A} + \overline{B}$ in positive logic.

The SN54AHCT00 is characterized for operation over the full military temperature range of –55°C to 125°C. The SN74AHCT00 is characterized for operation from –40°C to 85°C.

SN54AHCT00 . . . J OR W PACKAGE SN74AHCT00 . . . D, DB, DGV, N, OR PW PACKAGE (TOP VIEW)



SN54AHCT00 . . . FK PACKAGE (TOP VIEW)



NC – No internal connection

FUNCTION TABLE (each gate)

	` -	
INP	JTS	OUTPUT
Α	В	Υ
Н	Н	W// L
CLD.	Χ	Н
X	L	Н

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

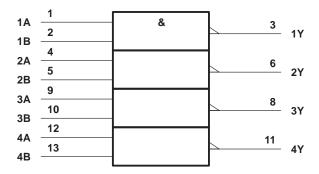
PIC is a trademark of Texas Instruments Incorporated.



SN54AHCT00, SN74AHCT00 QUADRUPLE 2-INPUT POSITIVE-NAND GATES

SCLS229H - OCTOBER 1995 - REVISED JANUARY 2000

logic symbol†



[†] This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12. Pin numbers shown are for D, DB, DGV, J, N, PW, and W packages.

logic diagram, each gate (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)‡

Supply voltage range, V _{CC}		
Output voltage range, V _O (see Note 1)		
Input clamp current, I_{IK} ($V_I < 0$)		
Output clamp current, I _{OK} (V _O < 0 or V _O > V _{CO}	c)	±20 mA
Continuous output current, $I_O(V_O = 0 \text{ to } V_{CC})$	·	±25 mA
Continuous current through V _{CC} or GND		±50 mA
Package thermal impedance, θ_{JA} (see Note 2):	: D package	86°C/W
	DB package	96°C/W
	DGV package	127°C/W
	N package	80°C/W
	PW package	113°C/W
Storage temperature range, T _{sto}		–65°C to 150°C

[‡] Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

2. The package thermal impedance is calculated in accordance with JESD 51.



SN54AHCT00, SN74AHCT00 QUADRUPLE 2-INPUT POSITIVE-NAND GATES

SCLS229H - OCTOBER 1995 - REVISED JANUARY 2000

recommended operating conditions (see Note 3)

		SN54AI	НСТ00	SN74AI	UNIT		
		MIN	MAX	MIN	MAX	CIVIT	
Vcc	Supply voltage	4.5	5.5	4.5	5.5	V	
VIH	High-level input voltage	2		2		V	
V _{IL}	Low-level input voltage		0.8		0.8	V	
٧ _I	Input voltage	0	5.5	0	5.5	V	
Vo	Output voltage	0	VCC	0	VCC	V	
Іон	High-level output current		-8		-8	mA	
loL	Low-level output current		8		8	mA	
Δt/Δν	Input transition rise or fall rate		20		20	ns/V	
T _A	Operating free-air temperature	-55	125	-40	85	°C	

NOTE 3: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	vcc	T _A = 25°C			SN54AHCT00		SN74AHCT00		UNIT
	TEST CONDITIONS		MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNII
VOH	I _{OH} = -50 μA	4.5 V	4.4	4.5		4.4		4.4		V
	I _{OH} = -8 mA	4.5 V	3.94			3.8		3.8		
VOL	I _{OL} = 50 μA	4.5 V			0.1		0.1		0.1	V
	I _{OL} = 8 mA	4.5 V			0.36		0.44		0.44	
lį	$V_I = V_{CC}$ or GND	0 V to 5.5 V			±0.1		±1*		±1	μΑ
Icc	$V_I = V_{CC}$ or GND, $I_O = 0$	5.5 V			2		20		20	μΑ
∆l _{CC} †	One input at 3.4 V, Other inputs at V _{CC} or GND	5.5 V			1.35		1.5		1.5	mA
Ci	V _I = V _{CC} or GND	5 V		2	10				10	pF

^{*} On products compliant to MIL-PRF-38535, this parameter is not production tested at $V_{CC} = 0 \text{ V}$.

switching characteristics over recommended operating free-air temperature range, V_{CC} = 5 V \pm 0.5 V (unless otherwise noted) (see Figure 1)

PARAMETER	FROM		LOAD CAPACITANCE	TO LOAD		ղ = 25°C	;	SN54AI	НСТ00	SN74AI	HCT00	UNIT		
PARAMETER	(INPUT)			MIN	TYP	MAX	MIN	MAX	MIN	MAX	UNIT			
tPLH	A or B	A or B	V	C 15 pE		5**	6.9**	1**	8**	1	8	no		
^t PHL			'	'	ı	1 Ο[= 13 β1	C _L = 15 pF	OL = 13 pr		5**	6.9**	1**	8**	1
^t PLH	A or B	V	C 50 pE		5.5	7.9	1	9	1	9	no			
tPHL		ſ	$C_L = 50 pF$		5.5	7.9	1	9	1	9	ns			

^{**} On products compliant to MIL-PRF-38535, this parameter is not production tested.



[†] This is the increase in supply current for each input at one of the specified TTL voltage levels rather than 0 V or V_{CC}.

SN54AHCT00, SN74AHCT00 QUADRUPLE 2-INPUT POSITIVE-NAND GATES

SCLS229H - OCTOBER 1995 - REVISED JANUARY 2000

noise characteristics, V_{CC} = 5 V, C_L = 50 pF, T_A = 25°C (see Note 4)

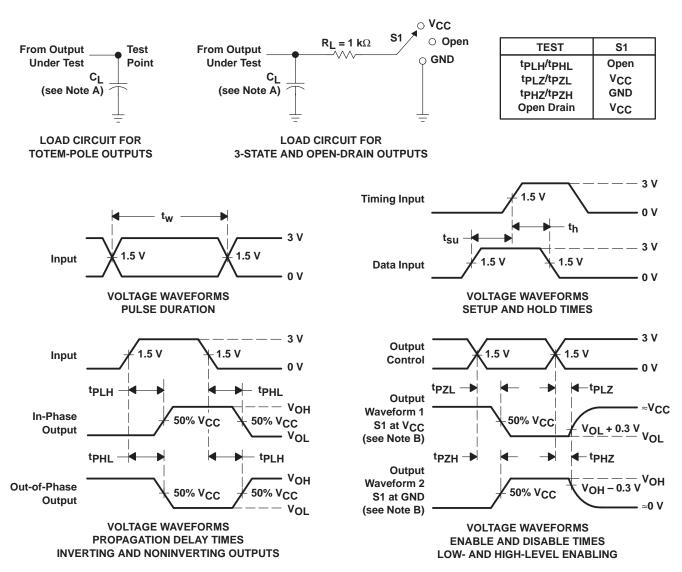
	PARAMETER				UNIT
					UNIT
VOL(P)	Quiet output, maximum dynamic VOL		0.4	0.8	V
V _{OL(V)}	Quiet output, minimum dynamic V _{OL}		-0.4	-0.8	V
V _{OH(V)}	Quiet output, minimum dynamic V _{OH}		4.5		V
VIH(D)	High-level dynamic input voltage	2			V
V _{IL(D)}	Low-level dynamic input voltage			0.8	V

NOTE 4: Characteristics are for surface-mount packages only.

operating characteristics, V_{CC} = 5 V, T_A = 25°C

	PARAMETER	TEST CC	NDITIONS	TYP	UNIT
C _{pd}	Power dissipation capacitance	No load,	f = 1 MHz	10.5	pF

PARAMETER MEASUREMENT INFORMATION



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 1 MHz, $Z_Q = 50 \Omega$, $t_f \leq$ 3 ns, $t_f \leq$ 3 ns.
- D. The outputs are measured one at a time with one input transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms



IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgement, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its semiconductor products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

CERTAIN APPLICATIONS USING SEMICONDUCTOR PRODUCTS MAY INVOLVE POTENTIAL RISKS OF DEATH, PERSONAL INJURY, OR SEVERE PROPERTY OR ENVIRONMENTAL DAMAGE ("CRITICAL APPLICATIONS"). TI SEMICONDUCTOR PRODUCTS ARE NOT DESIGNED, AUTHORIZED, OR WARRANTED TO BE SUITABLE FOR USE IN LIFE-SUPPORT DEVICES OR SYSTEMS OR OTHER CRITICAL APPLICATIONS. INCLUSION OF TI PRODUCTS IN SUCH APPLICATIONS IS UNDERSTOOD TO BE FULLY AT THE CUSTOMER'S RISK.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such semiconductor products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, warranty or endorsement thereof.

Copyright © 2000, Texas Instruments Incorporated